

III-V MOVPE for RF power applications

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Abstract

Over the years, metal organic vapor phase epitaxy has evolved into a mature high volume production technology for electronic devices, capable of very high quality, high repeatability, extreme accuracy for the whole range of III-V materials and electronic devices at low cost.

The roadmap of applications to RF power amplifiers based on PHEMT and HBT on GaAs, InP and metamorphic layers will be discussed.